TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))	Docket No. BUR920030031US1									
In Re Application Of: Anderson et al.										
Serial No. Filling Date TRAILER Examiner	Group Art Unit									
Title: METHOD OF FORMING FREESTANDING SEMICONDUCTOR LAYER										
Address to: Assistant Commissioner for Patents Washington, D.C. 20231										
37 CFR 1.97(b)										
The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application other than a continued prosecution application under 37 CFR 1.53(d); within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; before the mailing of a first Office Action on the merits, or before the mailing of a first Office Action after the filing of a request for continued examination under 37 CFR 1.114.										
37 CFR 1.97(c)										
CFR 1.97(b), provided that the Information Disclosure Statement is filed before Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR	The Information Disclosure Statement submitted herewith is being filed after the period specified in 37 CFR 1.97(b), provided that the Information Disclosure Statement is filed before the mailing date of a Final Action under 37 CFR 1.113, a Notice of Allowance under 37 CFR 1.311, or an Action that otherwise closes prosecution in the application, and is accompanied by one of:									
☐ the statement specified in 37 CFR 1.97(e);										
OR										
☐ the fee set forth in 37 CFR 1.17(p).										

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		Doo, V.Y., "Method of December 1981, pp. 34	Making Submic 107-3408.	ron Channe	I MOSFET," IBM T	Fechnical Disclosu	e Bulletin, Vol.	24, No. 7A	,		
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EXAMINER				DATE CONSIDERED							
EXAMINE	R: Initia	al if citation considered, whether	or not citation is i	n conforman	ce with MPEP Section (609; Draw line throu	gh citation if not	in conforma	nce and		
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